



# Bipolar PNP Bare Die – BTP6096

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## Part Description

The BTP6096 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN6096

## Key Parameters:

- VCBO = -80V
- VCEO = -60V
- VEBO = -5V
- hFE = 130-300 @ VCE = -5V, IC = -0.5A
- VCE(Sat) = -0.6V @ IC = -1A, IB = -100mA
- fT = 150 MHz @ VCE = -10V, IE = 0A
- COBO = 12pF @ VCB = -10V

## Features

Low VCE(sat). Designed to provide performance equivalent to ZETEX / DIODES INC. FM591

## Die Size (Unawn)

660µm X 660µm, 26 Mils X 26 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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